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#### **PJL9418 30V N-Channel Enhancement Mode MOSFET** SOP-8 30 V Current 18 A Voltage Features • $R_{DS(ON)}$ , $V_{GS}@10V$ , $I_D@18A < 2.4m\Omega$ • R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V,I<sub>D</sub>@9A<3.3mΩ • High switching speed • Improved dv/dt capability • Low Gate Charge • Low reverse transfer capacitance • Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive) • Green molding compound as per IEC61249 Std.. (Halogen Free) **Mechanical Data** • Case: SOP-8 package • Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0029 ounces, 0.083 grams

## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current	T <sub>A</sub> =25°C	_	18	
	T <sub>A</sub> =70°C	I <sub>D</sub>	14	A
Pulsed Drain Current <sup>(Note 1)</sup>		I <sub>DM</sub>	72	
Power Dissipation	T <sub>A</sub> =25°C	_	1.7	
	T <sub>A</sub> =70°C	P <sub>D</sub>	1.1	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 5)</sup>		R <sub>θJA</sub>	73.5	°C/W



#### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	<sub>SS</sub> V <sub>GS</sub> =0V,I <sub>D</sub> =250uA 30	-	-	v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1	1.6	2.5	v
Drain-Source On-State Resistance	$R_{DS(on)}$	V <sub>GS</sub> =10V,I <sub>D</sub> =18A	-	1.9	2.4	
Drain-Source On-State Resistance	$R_{DS(on)}$	V <sub>GS</sub> =4.5V,I <sub>D</sub> =9A	-	2.4	3.3	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg	V <sub>DS</sub> =15V, I <sub>D</sub> =18A, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	35	-	
Gate-Source Charge	$Q_{gs}$		-	13	-	nC
Gate-Drain Charge	$Q_gd$		-	10	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	4305	-	
Output Capacitance	Coss		-	617	-	pF
Reverse Transfer Capacitance	Crss		-	310	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}=15V, I_{D}=1A,$ $V_{GS}=10V, R_{G}=1\Omega$ (Note 2.3)	-	13	-	
Turn-On Rise Time	tr		-	14	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	46	-	ns
Turn-Off Fall Time	tf		-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	18	А
Diode Forward Current	I <sub>S</sub>		-	-	10	~
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.66	1	V

NOTES :

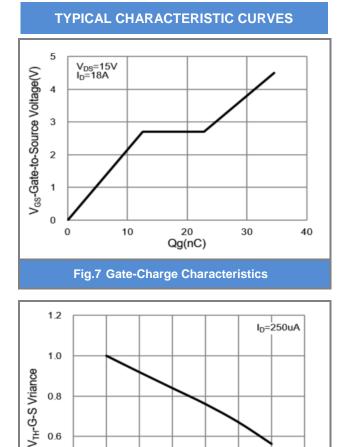
- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

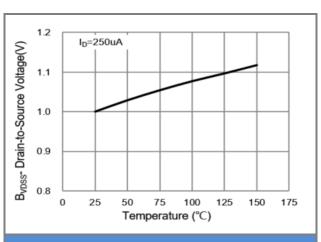




#### **PJL9418 TYPICAL CHARACTERISTIC CURVES** 20 20 1¢V,8V,5V,4 5V y₀s=3∨ V<sub>DS</sub>=5V Ips-Drain-to-S ource Current(A) I<sub>DS</sub>-Drain-to-S ource Current(A) 15 15 V<sub>GS</sub>=2.5V 10 10 T\_=25℃ T\_=125℃ 5 5 0 0 0 2 3 1 4 5 0 1 3 2 4 V<sub>DS</sub>- Drain-to-Source Voltage(V) V<sub>GS</sub>-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 4.5 2.5 R<sub>Ds</sub>(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m $\Omega$ ) 3.5 2.0 V<sub>GS</sub>=10V, I<sub>D</sub>=18A V<sub>GS</sub>= 4.5V 2.5 1.5 V<sub>GS</sub>= 10V V<sub>GS</sub>=4.5V, I<sub>D</sub>=9Å 1.5 1.0 0.5 0.5 0 5 10 15 20 0 25 50 75 100 125 150 175 I<sub>DS</sub>-Drain-to-Source Current(A) Temperature (°C) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 8 10 I<sub>D</sub>=10A I<sub>sD</sub>-Source to Drain Current(A) R<sub>Ds</sub>(on)- On-Resistance(mΩ) 6 1 4 T<sub>i</sub>=125℃ Tj=125℃ Tj=25℃ 0.1 Tj=25℃ 2 0.01 0 0 0 2 4 6 8 10 0.3 0.6 0.9 1.2 V<sub>GS</sub>-Gate-to-Source Voltage(V) V<sub>SD</sub>-Source-to-Drain Voltage(V) **Fig.6 Body Diode Characteristics**

Fig.5 On-Resistance Variation with VGS







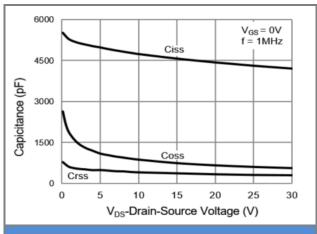


Fig.10 Capacitance vs. Drain-Source Voltage

0.8

0.6

0.4

0

25

50

75

Fig.9 Threshold Voltage Variation with Temperature

Temperature (°C)

100

125

150

175

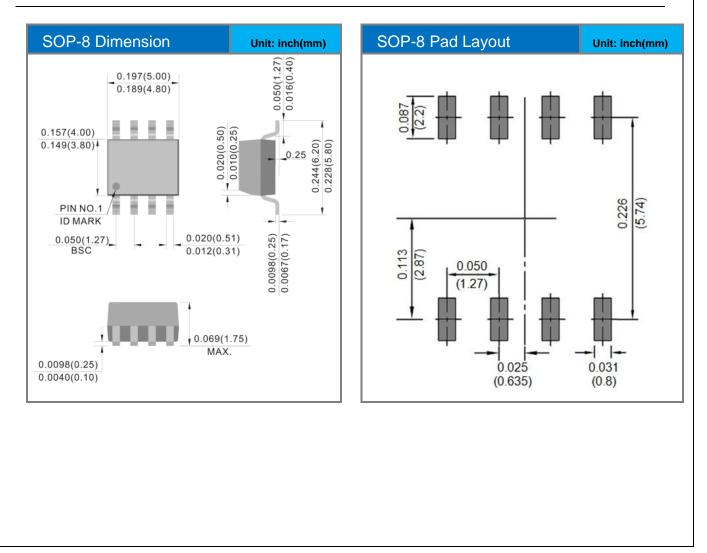




#### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJL9418_R2_00001	SOP-8	2.5K pcs / 13" reel	L9418	Halogen free

#### Packaging Information & Mounting Pad Layout





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